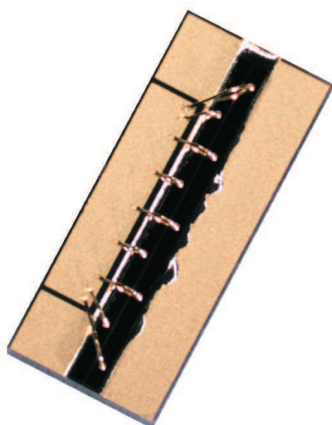


LU0977S650

Single Mode Laser Chip on Submount Up to 650 mW Operating Power



Description:

The Lumics single mode laser chip on submount contains an optimized GaAs/AlGaAs/InGaAs quantum well high power laser. It has been specifically designed for applications in low noise broadband Erbium Doped Fiber Amplifiers (EDFA). The extremely stringent reliability requirements are achieved through our patent pending innovative technology. This includes careful design, exactly defined manufacturing and extensive testing. The qualification contains a set of optoelectronic, thermal and mechanical tests. Each laser chip is individually serialized for traceability and is shipped with a specified set of test data.

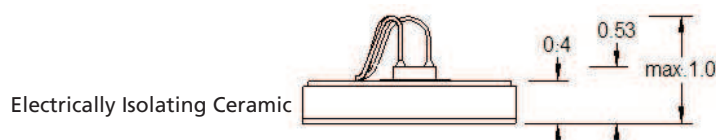
Features:

- Wavelengths: 970 - 985nm
- Kink-free power up to 730mW

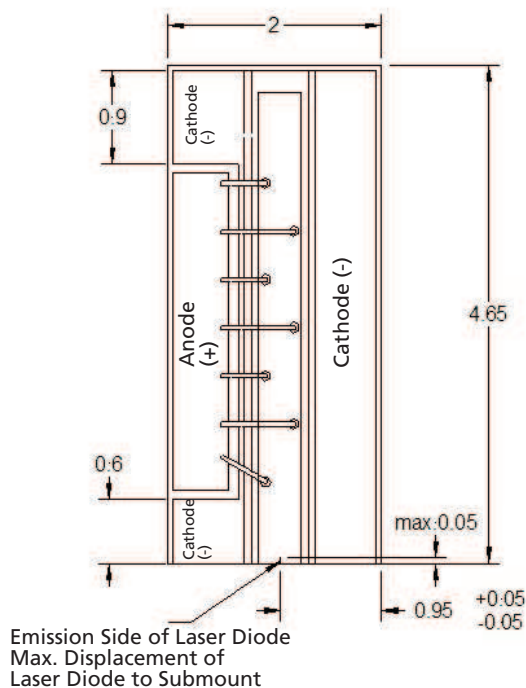
Benefits:

- Proven Reliability for High Power Operation
- Suited for cooled and uncooled Operation
- Telcordia GR-468-CORE

Module Drawing (Dimensions in mm)



Optical Height of Emitter 0.53mm



- (1) Anode and cathode isolated from bottom metallization
- (2) Top and bottom metallization >0.9μm Au plating for wire bonding and soldering

We manufacture diode lasers.

Characteristics (Top = 25°C)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Threshold Current		I _{th}		75	85	mA
Characteristic Temp.		T ₀	110			K
Forward Voltage	at I _{op} , Top	V _{op}		1.6	1.7	V
Slope Efficiency	at I _{op} , Top	η _{diff}		0.9		W / A
Peak Wavelength	at I _{op} , Top	λ _{peak}	970		985	nm
Spectral Width	at I _{op} , Top	FWHM		0.3		nm
Electrical Field Vector Orientation	in expitaxial plane			TE		
Polarisation Extinction Ratio		PER	20			dB
Lateral Farfield (FWHM)	at I _{op} , Top	Δ⊙II	6	8	10	deg
Vertical Farfield (FWHM)	at I _{op} , Top	Δ⊙⊥		28	33	deg
AR Reflectivity		r _f		0.2		%
HR Reflectivity		r _r		95		%
Spectral Shift with Current		λ _I Shift		0.007		nm / mA
Spectral Shift with Temp.		λ _T Shift		0.3		nm / K

Operating Parameters

Product Code	Operating Power (1) P _{op} [mW]	Max. Operating Current I _{op} [mA] BOL	EOL	Min. Kink free Power (2) P _k [mW]
LU0980S650	650	800	850	730

Note:

- (1) Operating current (power) is the maximum current (power) where the slope efficiency does not decrease by more than 20% from average between 1.8x - 4.5x threshold to 110% of the maximum rated output power.
- (2) Kink-free is defined as $I_{DL}/I < 0.2$, where I_{DL} is the average slope efficiency below kink.

Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit
Forward Current	I _F , max		900	mA
Reverse Voltage	V _R , max		2	V
Operating Temp.	T _{op}	-10	70	°C
Storage Temp.	T _{max}	-10	85	°C
Processing Temp.	T _S , max		260	°C
Submount, max. 10 sec.				

Note:

- (1) Absolute maximum ratings may be applied to the laser module for short period of time only. Exposure to maximum ratings for extended period of time or exposure above one or more max ratings may cause damage or affect the reliability of the device.
- (2) LD reliability is a function of the operating temperature and current
- (3) Storage and operation in non condensing environment only such that the environmental temperature is below the dew point

User Safety



We manufacture diode lasers.